

# MH2M08BPNA-7,-8

16777216-BIT(2097152-WORD BY 8-BIT)PSEUDO-PSEUDO STATIC RAM

## DESCRIPTION

The MH2M08BPNA is 2097152-word × 8-bit PSEUDO-PSEUDO static RAM and consist of four industry standard 1M × 4 bit dynamic RAMs in SOJ, two data selector in SOP and one DRAM controller in SOP. The mounting of SOJ and SOP on a dual in-line package provides any application where high densities and large quantities of memory are required.

## FEATURES

Type	Access time (max) Note 1	power dissipation (typ)
MH2M08BPNA-7	106ns	750mW
MH2M08BPNA-8	116ns	650mW

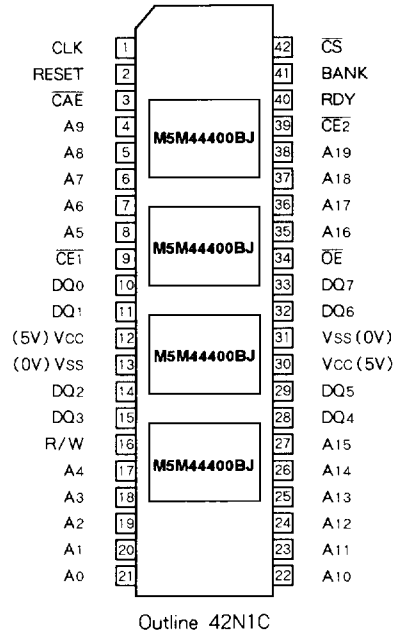
Note 1: When Wait Operation, Access time is measured from end of T1 of clock.

- Single +5V (±10%) supply operation
- 42-pin 600 mil Dual in-line package
- No refresh
- All inputs and outputs are directly TTL compatible
- Includes (0.22 μF × 7) decoupling capacitors

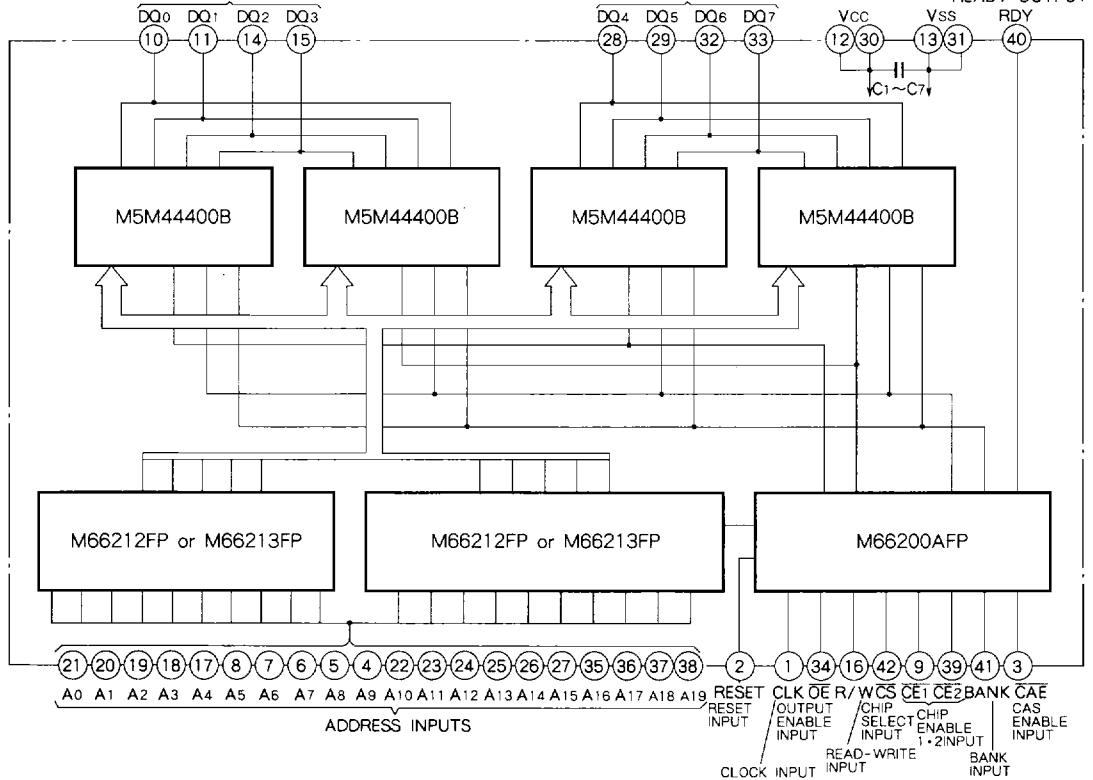
## APPLICATION

Small Capacity Memory Units

## PIN CONFIGURATION(TOP VIEW) (Both side)



## BLOCK DIAGRAM



**16777216-BIT(2097152-WORD BY 8-BIT)PSEUDO-PSEUDO STATIC RAM**

**FUNCTION**

MH2M08BPNA Series is 2097152 word by 8-bit. These devices operate on a single 5V supply, and all inputs and outputs are directly TTL compatible.

When DRAM controller counted 117th clock pulse from CLK terminal, DRAM is automatically refreshed. Accordingly, Outside refreshing is not required.

Multiplexer enable to put separate address in as SRAM.

Internal action of the MH2M08BPNA is of the same period as clock pulse and 1 state(time of one read or write cycle) consists of 4 clock pulses.

A write cycle is executed whenever the low level  $\overline{CE1}$  overlaps with the low level  $\overline{CS}$  at the last "H" → "L" edge of T<sub>1</sub> (first clock pulse of write cycle). The address is

determined by BANK and A<sub>0</sub>~A<sub>19</sub>.

The data is latched into a cell on the last "H" → "L" edge of T<sub>2</sub> (second clock pulse of write cycle) requiring the set-up and hold time relative to this edge to be maintained.

A read cycle is executed whenever the low level  $\overline{CE2}$  overlaps with the low level  $\overline{CS}$  at the last "H" → "L" edge of T<sub>1</sub>. When address is determined by BANK and A<sub>0</sub>~A<sub>19</sub> data situated on the address is read.

When setting  $\overline{CS}$  at high level or  $\overline{CE1}$  and  $\overline{CE2}$  at the same time at high level, the chip is in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in floating state.

**DESCRIPTION OF PINS**

Symbol	I/O	Function																								
RESET		Reset input This input resets built-in flip and is active H.																								
CLK		Clock input																								
$\overline{CS}$ $\overline{CE1}$ , $\overline{CE2}$		Decode signal of CPU address Status signal from CPU The memory access cycle is started by $\overline{CS}$ , $\overline{CE1}$ and $\overline{CE2}$ signals. <table border="1" style="margin: 10px auto;"> <thead> <tr> <th><math>\overline{CS}</math></th> <th><math>\overline{CE1}</math></th> <th><math>\overline{CE2}</math></th> <th>Mode</th> </tr> </thead> <tbody> <tr> <td>H</td> <td>Don't care</td> <td>Don't care</td> <td>No-access</td> </tr> <tr> <td>L</td> <td>L</td> <td>L</td> <td>Read</td> </tr> <tr> <td>L</td> <td>L</td> <td>H</td> <td>Write</td> </tr> <tr> <td>L</td> <td>H</td> <td>L</td> <td>Read</td> </tr> <tr> <td>L</td> <td>H</td> <td>H</td> <td>No-access</td> </tr> </tbody> </table>	$\overline{CS}$	$\overline{CE1}$	$\overline{CE2}$	Mode	H	Don't care	Don't care	No-access	L	L	L	Read	L	L	H	Write	L	H	L	Read	L	H	H	No-access
$\overline{CS}$	$\overline{CE1}$	$\overline{CE2}$	Mode																							
H	Don't care	Don't care	No-access																							
L	L	L	Read																							
L	L	H	Write																							
L	H	L	Read																							
L	H	H	No-access																							
$\overline{OE}$		Read signal from CPU (assumed that read cycle finish)																								
R/W		Write signal from CPU (assumed that write cycle finish)																								
BANK CAE		Determine the valid combination of $\overline{RAS}$ , BANK change Determine the valid combination of $\overline{CAS}$ $\overline{CAS}$ is output by active L. <table border="1" style="margin: 10px auto;"> <thead> <tr> <th>BANK</th> <th><math>\overline{CAE}</math></th> <th>Memory area</th> </tr> </thead> <tbody> <tr> <td>Don't care</td> <td>H</td> <td>-</td> </tr> <tr> <td>L</td> <td>L</td> <td>BANK<sub>0</sub></td> </tr> <tr> <td>H</td> <td>L</td> <td>BANK<sub>1</sub></td> </tr> </tbody> </table>	BANK	$\overline{CAE}$	Memory area	Don't care	H	-	L	L	BANK <sub>0</sub>	H	L	BANK <sub>1</sub>												
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Don't care	H	-																								
L	L	BANK <sub>0</sub>																								
H	L	BANK <sub>1</sub>																								
A <sub>0</sub> ~A <sub>19</sub>		Address signal																								
RDY	Output	Read signal to CPU																								
DQ <sub>0</sub> ~7	Input/Output	Data input/output signal																								

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**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Condition	Ratings	Unit
V <sub>CC</sub>	Supply voltage	With respect to V <sub>SS</sub>	-1~7.0	V
V <sub>I</sub>	Input voltage		-1~7.0	V
V <sub>O</sub>	Output voltage		-1~7.0	V
I <sub>IK</sub>	Input protection diode current	V <sub>I</sub> < 0V	-20	mA
		V <sub>I</sub> > V <sub>CC</sub>	+20	
I <sub>O</sub>	Output current		50	mA
P <sub>d</sub>	Power dissipation	T <sub>a</sub> = 25°C	3500	mW
T <sub>opr</sub>	Operating temperature		0~70	°C
T <sub>stg</sub>	Storage temperature		-40~125	°C

**RECOMMENDED OPERATING CONDITIONS** (T<sub>a</sub> = 0~70°C unless otherwise noted) (Note 2)

Symbol	Parameter	Limits			Unit
		Min	Typ	Max	
V <sub>CC</sub>	Supply voltage	4.5	5	5.5	V
V <sub>SS</sub>	Supply voltage		0		V
V <sub>I</sub>	Input voltage	0		V <sub>CC</sub>	V
V <sub>O</sub>	Output voltage	0		V <sub>CC</sub>	V

Note 2: All voltage values are with respect to V<sub>SS</sub>.

**ELECTRICAL CHARACTERISTICS** (T<sub>a</sub> = 0~70°C, V<sub>CC</sub> = 5V ± 10%, V<sub>SS</sub> = 0V, unless otherwise noted) (Note 3)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min	Typ	Max		
V <sub>T+</sub>	Threshold voltage (RESET)	V <sub>O</sub> = 0.1, V <sub>CC</sub> = 0.1V, I <sub>O</sub> = 20 μA			2.4	V	
V <sub>T-</sub>	Threshold voltage (RESET)	V <sub>O</sub> = 0.1, V <sub>CC</sub> = 0.1V, I <sub>O</sub> = 20 μA	0.6			V	
V <sub>T+</sub> -V <sub>T-</sub>	Hysteresis width (RESET)	V <sub>O</sub> = 0.1, V <sub>CC</sub> = 0.1V, I <sub>O</sub> = 20 μA	0.2		1.8	V	
V <sub>IH</sub>	High input voltage (other input)	V <sub>O</sub> = 0.1, V <sub>CC</sub> = 0.1V, I <sub>O</sub> = 20 μA	2.4			V	
V <sub>IL</sub>	Low input voltage (other input)	V <sub>O</sub> = 0.1, V <sub>CC</sub> = 0.1V, I <sub>O</sub> = 20 μA			0.8	V	
V <sub>OH</sub>	High output voltage	I <sub>CH</sub> = -5mA	2.4		V <sub>CC</sub>	V	
V <sub>OL</sub>	Low output voltage	I <sub>OL</sub> = 4.2mA	0		0.4	V	
I <sub>IH</sub>	High input current	V <sub>I</sub> = V <sub>CC</sub>			1.0	μA	
I <sub>IL</sub>	Low input current	V <sub>I</sub> = GND			1.0	μA	
I <sub>CC1</sub> (AV)	Average supply current from V <sub>CC</sub> operating (Note 4, 5)	MH2M08BPNA-7	Maximum repeating frequency, output open			175	mA
		MH2M08BPNA-8				155	
I <sub>CC2</sub> (1)	Average supply current from V <sub>CC</sub> , stand by	V <sub>I</sub> = 2.4V, 0.4V, Output open (Note 6)				16.7	mA
I <sub>CC2</sub> (2)(AV)		V <sub>I</sub> = V <sub>CC</sub> , GND, f = 10MHz, Output open (Note 4, 7)			7		
I <sub>CC3</sub> (AV)	Average supply current from V <sub>CC</sub> , CAS before RAS refreshing (Note 4)	MH2M08BPNA-7	Refresh cycling, output open (5 clock from 117th clock)			175	mA
		MH2M08BPNA-8				155	
C <sub>I(A)</sub>	Input capacitance, address inputs	V <sub>I</sub> = V <sub>SS</sub> , f = 1MHz V <sub>I</sub> = 25mVrms			16	pF	
C <sub>I</sub>	Input capacitance (except address inputs)				17	pF	
C <sub>I(DO)</sub>	Input/output capacitance, Data input/output inputs				25	pF	
C <sub>O(RDY)</sub>	Output capacitance, RDY inputs	V <sub>O</sub> = V <sub>SS</sub> , f = 1MHz, V <sub>I</sub> = 25mVrms			10	pF	

Note 3: Current flowing into IC is positive, out is negative.

4: I<sub>CC1</sub>(AV), I<sub>CC2</sub>(2)(AV), I<sub>CC3</sub>(AV) are dependent on frequency of clock pulse. Limits are measured at maximum frequency.

5: I<sub>CC1</sub>(AV) is dependent on output loading specified values are obtained with the output open.

6: Only one input set to this value, all other input fix V<sub>CC</sub> or GND.

7: The value is setting to I<sub>CC3</sub>, when it get in refresh cycle every 121 clock.

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**SWITCHING CHARACTERISTICS** (Ta = 0~70°C, Vcc = 5V ± 10%, Vss = 0V, unless otherwise noted) (Note 8)

Symbol	Parameter	Limits						Unit
		MH2M08BPNA-7			MH2M08BPNA-8			
		Min	Typ	Max	Min	Typ	Max	
f	Repeating frequency	3.8		16.7	3.8		14.5	MHz
tPLH	CLK, $\overline{OE}$ , R/W-RDY propagation time (Note 9)			36			36	ns
tPHL				36			36	ns
tCKA	CLK access time			106			116	ns
tOFF	Output disable time after $\overline{OE}$ high	40		60	40		60	ns

Note 8: After power-up an initial pause of 500  $\mu$ s and dummy cycle (Read or Write cycle by 8 times degrees) followed by CLK,  $\overline{CS}$ ,  $\overline{CE1}$ ,  $\overline{CE2}$ ,  $\overline{OE}$ , R/W cycles are required before proper device operation is achieved. It may add that cycle during the initial pause, but dummy cycle is required.

9: The values are measured at loading capacitance CL = 50pF.

**TIMING REQUIREMENTS** (Ta = 0~70°C, Vcc = 5V ± 10%, Vss = 0V, unless otherwise noted) (Notes 10, 11)

**Read, Write, Refresh Mode Cycle**

Symbol	Parameter	Limits						Unit
		MH2M08BPNA-7			MH2M08BPNA-8			
		Min	Typ	Max	Min	Typ	Max	
tCKL	CLK low pulse width	25		50	35		60	ns
tCKH	CLK high pulse width	25		50	35		60	ns
tCSS	CLK- $\overline{CS}$ setup time	20			20			ns
tCSH	CLK- $\overline{CS}$ hold time	20			20			ns
tCE1S	CLK- $\overline{CE1}$ setup time	20			20			ns
tCE1H	CLK- $\overline{CE1}$ hold time	20			20			ns
tCE2S	CLK- $\overline{CE2}$ setup time	20			20			ns
tCE2H	CLK- $\overline{CE2}$ hold time	20			20			ns
tOES	CLK- $\overline{OE}$ setup time	20			20			ns
tOEH	CLK- $\overline{OE}$ hold time	1.5CK+10		2.5CK-20	1.5CK+10		2.5CK-20	ns
tRWS	CLK-R/W setup time	20			20			ns
tRWH	CLK-R/W hold time	1.0CK+10		2.0CK-20	1.0CK+10		2.0CK-20	ns
tAS	CLK-ADDRESS setup time	20			20			ns
tAH	CLK-ADDRESS hold time (READ) (READ) CLK-ADDRESS hold time (WRITE) (WRITE)	50 0.5CK+50			50 0.5CK+50			ns
tBKS	CLK-BANK setup time	20			20			ns
tBKH	CLK-BANK hold time	20			20			ns
tCAS	CLK- $\overline{CAE}$ setup time	20			20			ns
tCAH	CLK- $\overline{CAE}$ hold time	20			20			ns
tDS	CLK-DATA setup time	0			0			ns
tDH	CLK-DATA hold time	50			50			ns
tT	Transition time (Note12)	1		50	1		50	ns
tREF	Refresh cycle time (every 121 clocks)	8.5		15.7	9.7		15.7	$\mu$ s

Note 10: The timing requirements are assumed tT = 5ns.

11: V1 = 1.3V is reference levels for measuring timing of input signals.

12: tT is measured between VIH(min) and VIL(max).

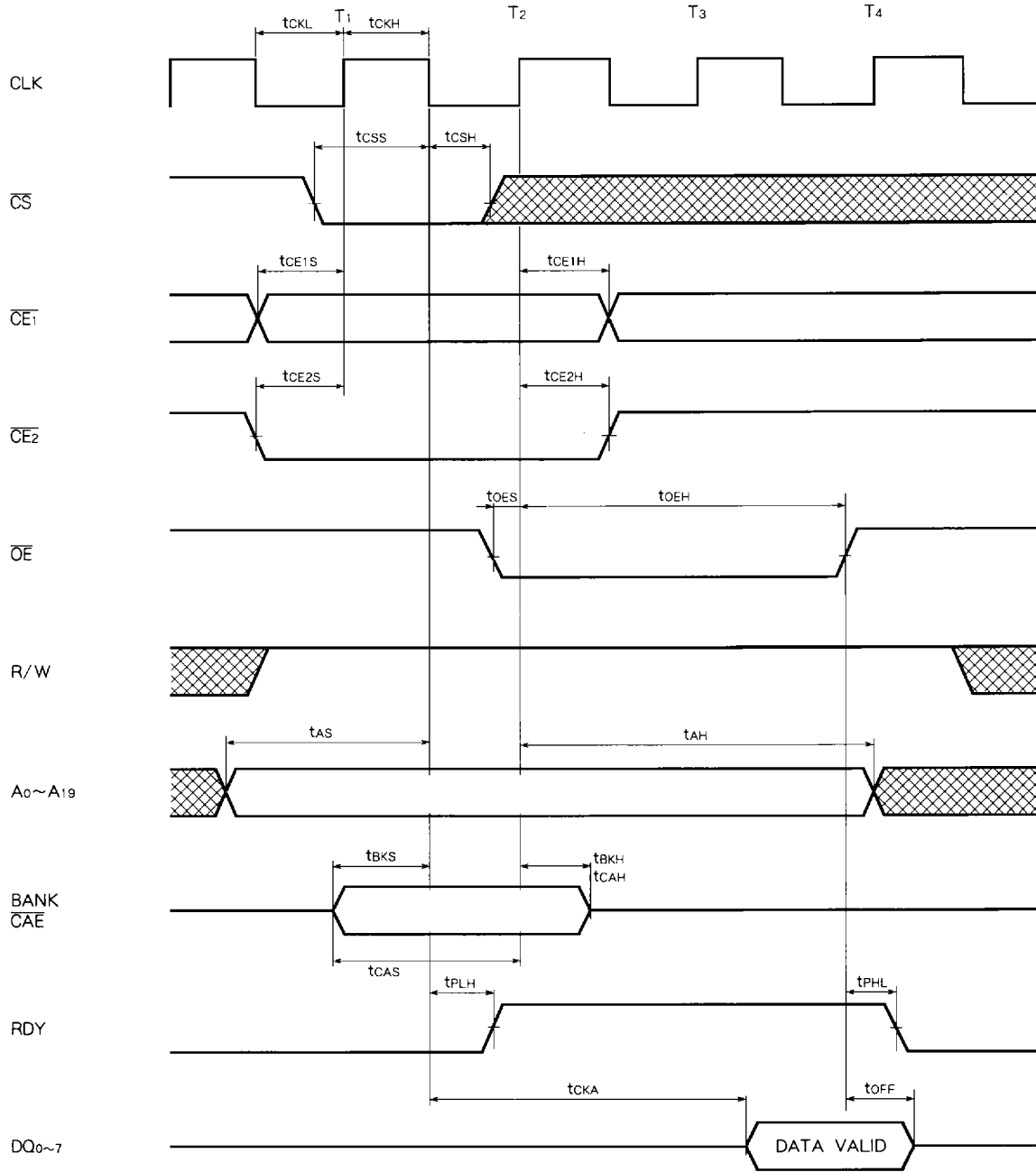
**Reset- Mode- Cycle**

Symbol	Parameter	Limits						Unit
		MH2M08BPNA-7			MH2M08BPNA-8			
		Min	Typ	Max	Min	Typ	Max	
tREW	RESET pulse width	20			20			ns
tREC	CLK-RESET recovery time	20			20			ns

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**TIMING DIAGRAM** (Note 13)

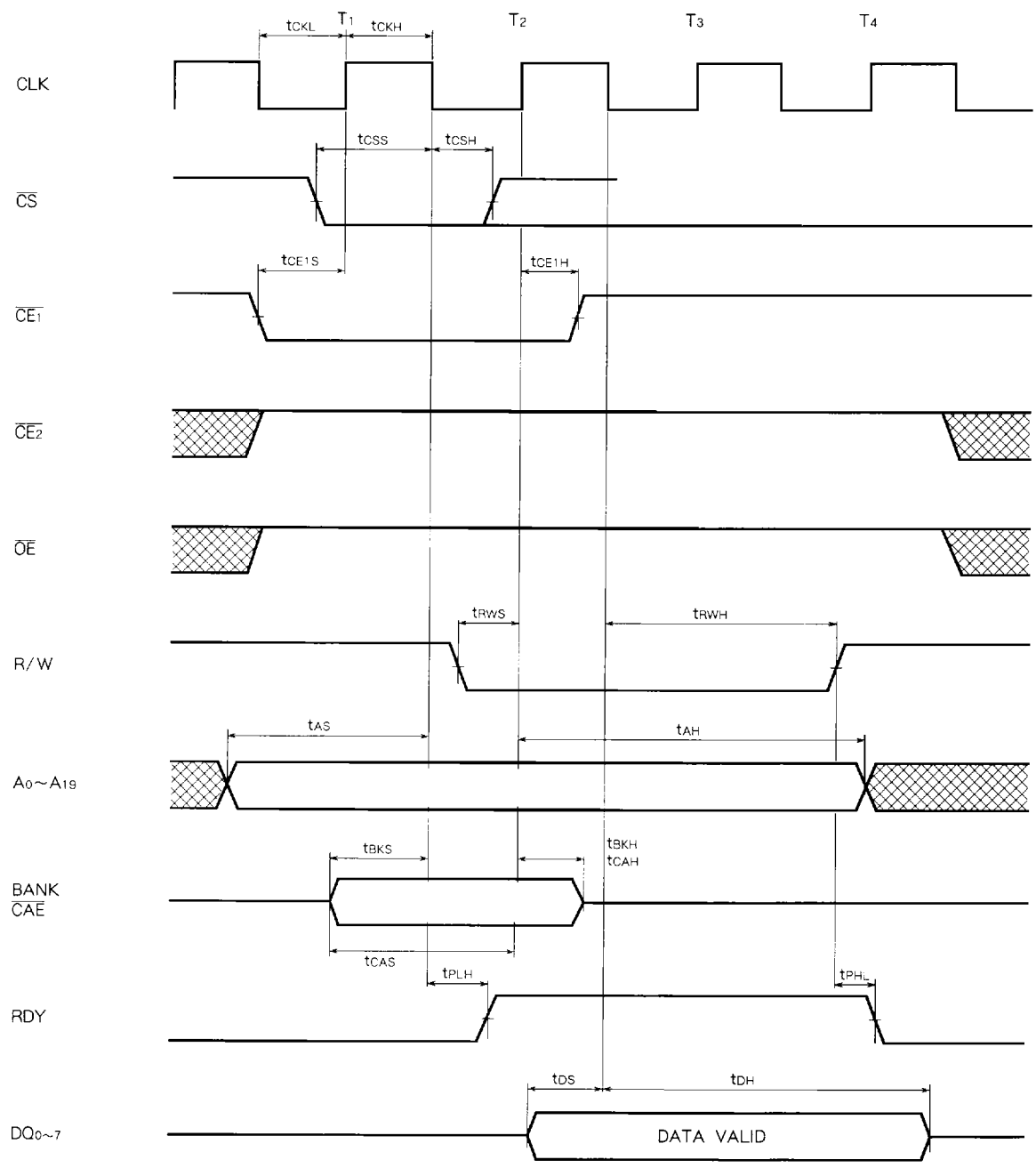
**Read Cycle**



Note 13 Indicates the don't care input.

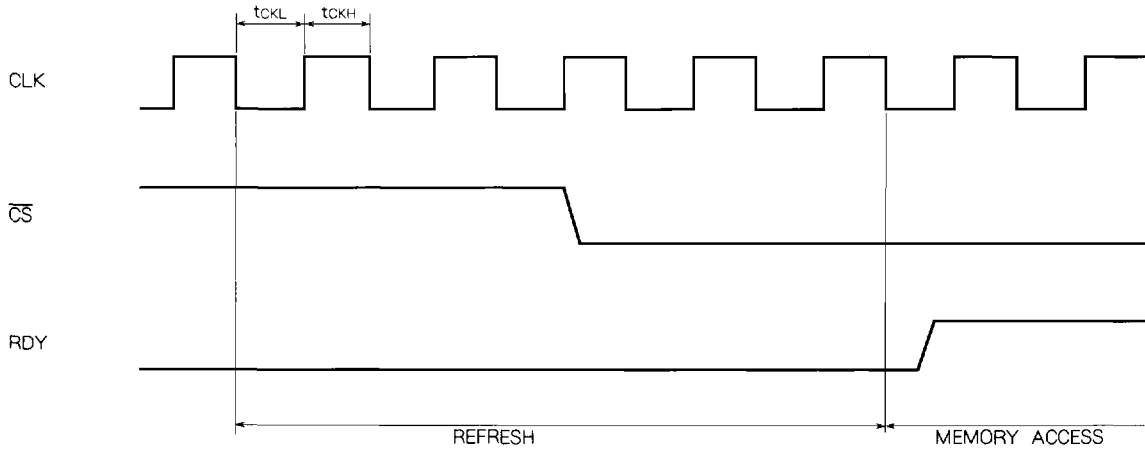
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**Write Cycle**



**1677216-BIT(2097152-WORD BY 8-BIT)PSEUDO-PSEUDO STATIC RAM**

**Refresh Cycle** (Note 14)



Note 14 : While refresh cycle, other input signal are waiting condition.

**Reset Cycle**

